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FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT	ATTORNEY DOCKET NO.: ASC-044 APPLICANT(S): Fitzgerald et al. SERIAL NO.: 09/884,172 FILING DATE: June 19, 2001 GROUP: 2822

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A46	4,010,045	3/1/1977	Ruehrwein			4/27/1976
	A47	4,997,776	3/1/1991	Harame et al.			6/20/1990
	A48	5,013,681	5/7/1991	Godbey et al.			9/29/1989
	A49	5,166,084	11/24/1992	Pfiester			9/3/1991
	A50	5,177,583	1/1/1993	Endo et al.			1/10/1991
	A51	5,202,284	4/1/1993	Kamins et al.			12/1/1989
	A52	5,207,864	5/4/1993	Bhat et al.			12/30/1991
	A53	5,208,182	5/4/1993	Narayan et al.			11/12/1991
	A54	5,212,110	5/18/1993	Pfiester et al.			5/26/1992
	A55	5,221,413	6/22/1993	Brasen et al.			4/24/1991
	A56	5,250,445	10/1/1993	Bean et al.			1/17/1992
	A57	5,285,086	2/1/1994	Fitzgerald			6/18/1992
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	A59	5,310,451	5/10/1994	Tejwani et al.			8/19/1993
	A60	5,346,848	9/13/1994	Grupen-Shemansky et al.			6/1/1993
	A61	5,374,564	12/20/1994	Bruel			12/20/1994
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	A63	5,413,679	5/9/1995	Godbey et al.			6/30/1993
	A64	5,426,069	6/20/1995	Selvakumar et al.			4/9/1992
	A65	5,461,243	10/24/1995	Ek et al.			10/29/1993
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	A71	5,630,905	5/1/1997	Lynch et al.			6/5/1995
	A72	5,659,187	8/1/1997	Legoues et al.			6/7/1995
	A73	5,714,777	2/3/1998	Ismail et al.			2/19/1997
	A74	5,728,623	3/17/1998	Mori			3/16/1995
	A75	5,759,898	6/2/1998	Ek et al.			12/19/1996
	A76	5,786,612	7/28/1998	Otani et al.			4/16/1996
	A77	5,877,070	3/2/1999	Goesele et al.			5/31/1997
	A78	5,906,708	5/25/1999	Robinson et al.			12/6/1995
	A79	5,943,560	8/24/1999	Chang et al.			4/19/1996
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	A83	6,074,919	6/13/2000	Gardner et al.			1/20/1999
	A84	6,103,559	8/15/2000	Gardner et al.			3/30/1999
	A85	6,133,799	10/17/2000	Favors, Jr., et al.			2/25/1999
	A86	6,140,687	10/31/2000	Shimomura et al.			11/26/1997
	A87	6,153,495	11/28/2000	Kub et al.			3/9/1998
	A88	6,154,475	11/28/2000	Soref et al.			12/4/1997
	A89	6,160,303	12/12/2000	Fattaruso			8/26/1998
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	A93	6,191,432	2/20/2001	Sugiyama et al.			9/2/1997
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	A95	6,210,988	4/3/2001	Howe et al.			1/14/2000
	A96	6,218,677	4/17/2001	Broekaert			8/15/1994
	A97	6,232,138	5/15/2001	Fitzgerald et al.			11/24/1998
	A98	6,235,567	5/22/2001	Huang			8/31/1999
	A99	6,261,929	7/1/2001	Gehrke et al.			2/24/2000
	A100	6,271,551	8/7/2001	Schmitz et al.			12/13/1996
	A101	6,271,726	8/7/2001	Fransis et al.			1/10/2000
	A102	6,313,016	11/6/2001	Kibbel et al.			12/22/1999
	A103	6,323,108	11/27/2001	Kub et al.			7/2719/99
	A104	6,329,063	12/11/2001	Lo et al.			12/11/1998
	A105	6,335,546	1/1/2002	Tsuda et al.			7/30/1998
	A106	6,368,733	4/9/2002	Nishinaga, Tatau			8/5/1999
	A107	6,372,356	4/16/2002	Thornton et al.			4/28/2000
	A108	6,403,975	6/11/2002	Brunner et al.			04/08/1997
	A109	6,425,951	7/30/2002	Chu et al.			8/6/1999
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	A113	2002/0140031	10/3/2002	Rim			3/31/2001
	A114	2002/0024395	02/28/2002	Akatsuka et al.			6/14/2001

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	A118	2002/0072130	6/13/2002	Cheng et al.			8/10/2001
	A119	2002/0096717	7/25/2002	Chu et al.			1/25/2001
	A120	2002/0100942	8/1/2002	Fitzgerald et al.			6/19/2001
	A121	2002/0123167	9/5/2002	Fitzgerald			7/16/2001
	A122	2002/0123183	9/5/2002	Fitzgerald			7/16/2001
	A123	2002/0123197	9/5/2002	Fitzgerald et al.			6/19/2001
	A124	2002/0125471	9/12/2002	Fitzgerald et al.			12/4/2001
	A125	2002/0125497	7/16/2002	Fitzgerald			7/16/2001
	A126	2002/0168864	11/14/2002	Cheng et al.			4/4/2002
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	A130	2003/0057439	03/27/2003	Fitzgerald			8/9/2002

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	B25	0 514 018	11/19/1992	EP				NO	YES
	B26	0 587 520	3/16/1994	EP				NO	YES
	B27	0 828 296	3/11/1998	EP				NO	YES
	B28	00/48239	8/17/2000	WO				NO	YES
	B29	01/22482	3/29/2001	WO				NO	YES

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B30	02/082514	10/17/2002	WO				NO	YES
	B31	02/27783	4/4/2002	WO				NO	YES
	B32	2 342 777	4/19/2000	GB				YES	YES
	B33	2 701 599	9/1/1993	FR				YES	YES
	B34	2000-031491	1/28/2000	JP				NO	NO
	B35	2002-076334	3/15/2002	JP				NO	YES
	B36	2002-164520	6/7/2002	JP				NO	YES
	B37	2002-289533	10/4/2002	JP				NO	YES
	B38	5-166724	07/23/1993	JP				NO	Abstract only
	B39	6-177046	06/24/1994	JP				NO	Abstract only
	B40	6-244112	09/02/1994	JP					
	B41	6-252046	09/09/1994	JP				NO	Abstract only
	B42	7-094420	04/07/1995	JP				NO	Abstract only
	B43	7-240372	09/12/1995	JP				NO	Abstract only

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EXAM. INIT.		OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)
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	C49	Augusto et al., "Proposal for a New Process Flow for the Fabrication of Silicon-based Complementary MOD-MOSFETs without ion Implantation," Thin Solid Films, vol. 294, no. 1-2, pp. 254-258 (February 15, 1997).
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	C55	Chang et al., "Selective Etching of SiGe/Si Heterostructures," Journal of the Electrochemical Society, No. 1 (January 1991) pp. 202-204.
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	C63	Ishikawa et al., "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," Applied Physics Letters, Vol. 75, No. 7 (August 16, 1999) pp. 983-985.
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	C75	Papananos, "Radio-Frequency Microelectronic Circuits for Telecommunication Applications", Kluwer Academic Publishers, 1999, pp. 115-117, 188-193.
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